



100V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	Package	I _D T _C = +25°C	
100V	$9.5 \text{m}\Omega @V_{GS} = 10V$	TO220AB	100A	

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

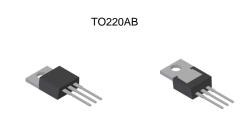
- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

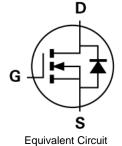
Features

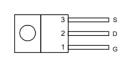
- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: TO220AB
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







Top View

Bottom View

Top View
Pin Out Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH10H010SCT	TO220AB	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine 1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



| Hanufacturer's Marking
| H10H010S = Product Type Marking Code
| YYWW = Date Code Marking
| YY or YY = Last Two Digits of Year (ex: 18 = 2018)
| WW or WW = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	100	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	ΙD	100 80	А
Maximum Continuous Body Diode Forward Current	T _C = +25°C	I _S	90	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	400	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	400	Α	
Avalanche Current, L = 0.3mH (Note 7)	I _{AS}	33.7	Α	
Avalanche Energy, L = 0.3mH (Note 7)	E _{AS}	170	mJ	

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)		RθJA	60	°C/W
Total Power Dissipation	$T_C = +25^{\circ}C$	P_{D}	187	W
Thermal Resistance, Junction to Case		R ₀ JC	0.8	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

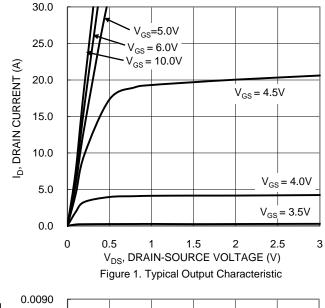
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 6)							
Drain-Source Breakdown Voltage	BV _{DSS}	100	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 6)						·	
Gate Threshold Voltage	V _{GS(TH)}	2	1	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	7.4	9.5	mΩ	$V_{GS} = 10V, I_D = 13A$	
Diode Forward Voltage	V_{SD}	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 13A$	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	_	4468		pF	$V_{DS} = 50V$, $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss	_	746	1			
Reverse Transfer Capacitance	C _{rss}	_	31.6	_			
Gate Resistance	R_g	_	0.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	56.4	_		V _{DD} = 50V, I _D = 13A, V _{GS} = 10V	
Gate-Source Charge	Q_{gs}	_	15.4	_	nC		
Gate-Drain Charge	Q_{gd}	_	14.0	_			
Turn-On Delay Time	t _{D(ON)}	_	18.6	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 13A, R_{g} = 6\Omega$	
Turn-On Rise Time	t _R	_	22.5	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	44.8	_			
Turn-Off Fall Time	t _F	_	29.5	_			
Reverse Recovery Time	t _{RR}	_	54.5	_	ns	I _F = 13A, di/dt = 100A/µs	
Reverse Recovery Charge	Q_{RR}	_	106.4	_	nC		

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

^{6.} Short duration pulse test used to minimize self-heating effect.

^{7.} Guaranteed by design. Not subject to product testing.





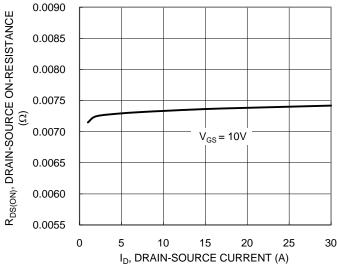


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

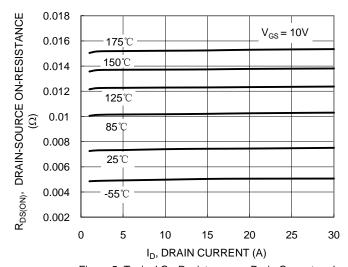


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

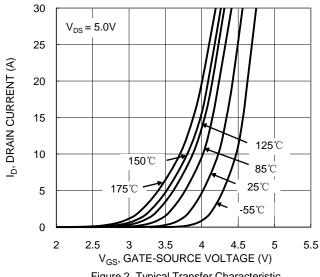


Figure 2. Typical Transfer Characteristic

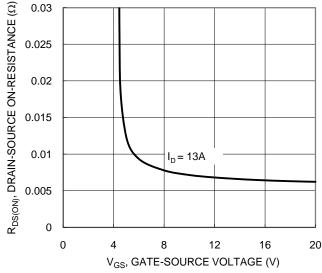


Figure 4. Typical Transfer Characteristic

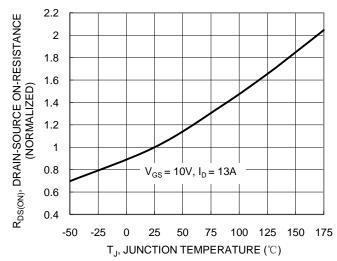


Figure 6. On-Resistance Variation with Temperature



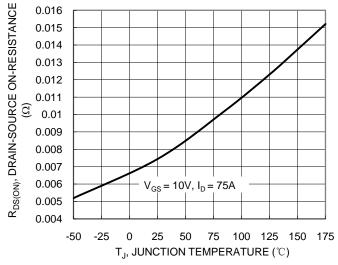


Figure 7. On-Resistance Variation with Temperature

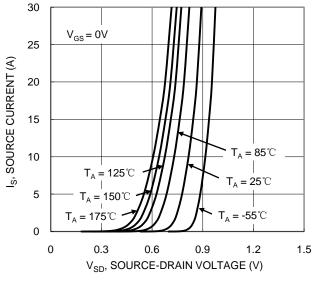


Figure 9. Diode Forward Voltage vs. Current

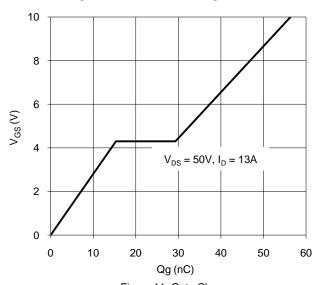


Figure 11. Gate Charge

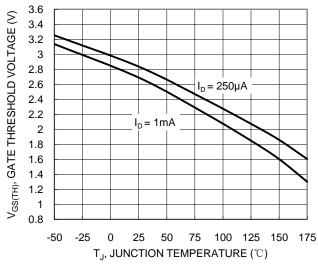


Figure 8. Gate Threshold Variation vs. JunctionTemperature

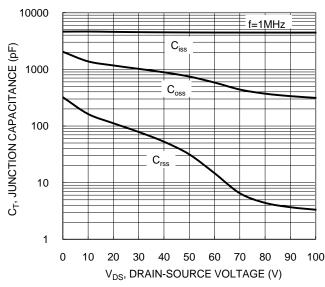
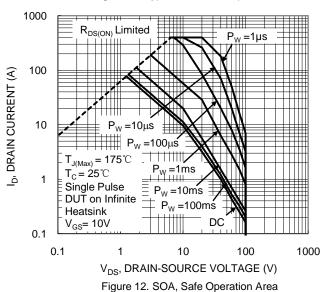
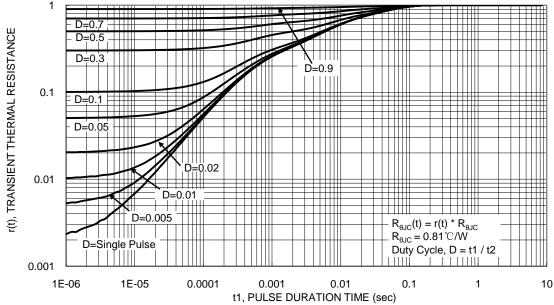


Figure 10. Typical Junction Capacitance





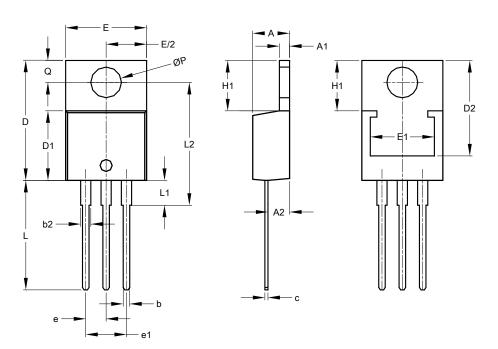




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB



TO220AB					
Dim	Min	Max	Тур		
Α	3.56	4.82	-		
A 1	0.51	1.39	-		
A2	2.04	2.92	-		
b	0.39	1.01	0.81		
b2	1.15	1.77	1.24		
С	0.356	0.61	-		
D	14.22	16.51	-		
D1	8.39	9.01	-		
D2	11.45	12.87	-		
е	-		2.54		
e1	-		5.08		
Е	9.66	10.66	-		
E1	6.86	8.89	-		
H1	5.85	6.85	-		
L	12.70	14.73	-		
L1	-	4.42	-		
L2	15.80	17.51	16.00		
Р	3.54	4.08	-		
Q	2.54	3.42	-		
All Dimensions in mm					



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